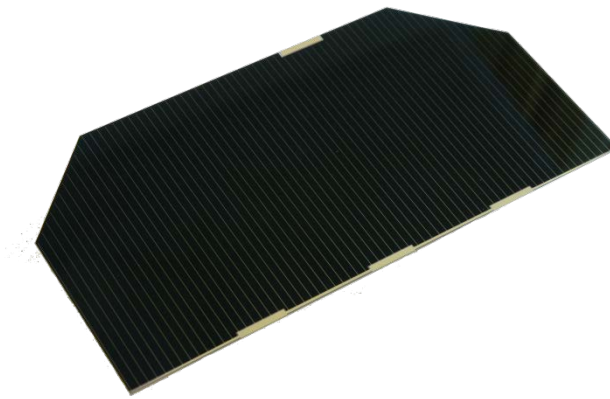




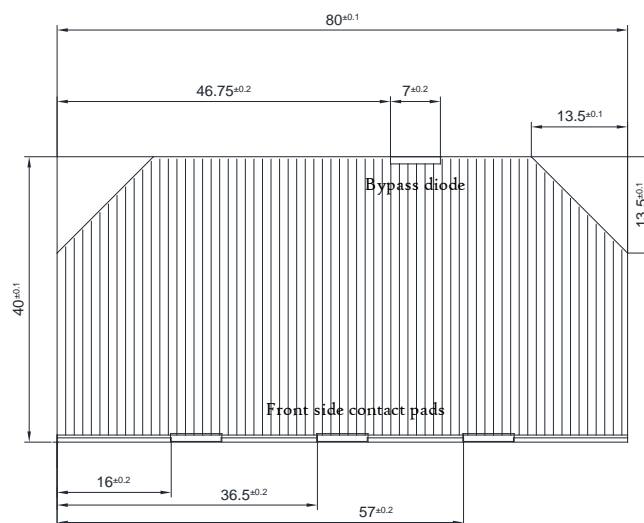
## 28% Triple Junction GaAs Solar Cell

### Type: TJ Solar Cell 3G28C

*More than 1 million 3G28C cells delivered*



This cell type is a GaInP/GaAs/Ge on Ge substrate triple junction solar cell (efficiency class 28%). The cell is equipped with an integrated bypass diode, which protects the adjacent cell in the string.



3G28C

# 28% Triple Junction GaAs Solar Cell

## Type: TJ Solar Cell 3G28C



### Design and Mechanical Data

|   |  |
|---|--|
| Base Material                           | GalnP/GaAs/Ge on Ge substrate                    |
| AR-coating                              | TiO <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> |
| Dimensions                              | 40 x 80 mm ± 0.1 mm                              |
| Cell Area                               | 30.18 cm <sup>2</sup>                            |
| Average Weight                          | ≤ 86 mg/cm <sup>2</sup>                          |
| Thickness (without contacts)            | 150 ± 20 µm                                      |
| Contact Metallization Thickness (Ag/Au) | 4 – 10 µm  |
| Grid Design                             | Grid system with 3 contact pads                  |



### Electrical Data

|   |      | BOL   | 2,5E14 | 5E14  | 1E15  |
|---|------|-------|--------|-------|-------|
| Average Open Circuit V <sub>oc</sub>                          | [mV] | 2667  | 2560   | 2534  | 2480  |
| Average Short Circuit I <sub>sc</sub>                         | [mA] | 506.0 | 500.9  | 500.9 | 485.8 |
| Voltage at max. Power V <sub>mp</sub>                         | [mV] | 2371  | 2276   | 2229  | 2205  |
| Current at max. Power I <sub>mp</sub>                         | [mA] | 487.0 | 482.1  | 472.4 | 457.8 |
| Average Efficiency η <sub>bare</sub> (1367 W/m <sup>2</sup> ) | [%]  | 28.0  | 26.6   | 25.5  | 24.5  |
| Average Efficiency η <sub>bare</sub> (1353 W/m <sup>2</sup> ) | [%]  | 28.3  | 26.9   | 25.8  | 24.7  |

Standard: CASOLBA 2005 (05-20MV1, etc); Spectrum: AMO WRC = 1367 W/m<sup>2</sup>; T = 28 °C

### Acceptance Values

|   |   |
|---|---|
| Voltage V <sub>op</sub>                                       | 2300 mV                                   |
| Min. average current I <sub>op avg</sub> @ V <sub>op</sub>    | 485 mA (higher I <sub>op</sub> on demand) |
| Min. individual current I <sub>op min</sub> @ V <sub>op</sub> | 455 mA                                    |

### Shadow protection

|                             |                                       |
|-----------------------------|---------------------------------------|
| Integrated protection diode | V <sub>forward</sub> (605 mA) ≤ 2.5 V |
| T = 25°C ± 3°C              | I <sub>reverse</sub> (2.8 V) ≤ 100µA  |



### Temperature Gradients (25°C - 80°C)

|                       |                               | BOL   | 2,5E14 | 5E14  | 1E15  |
|-----------------------|-------------------------------|-------|--------|-------|-------|
| Open Circuit Voltage  | ΔV <sub>oc</sub> /ΔT↑ [mV/°C] | - 6.0 | - 6.4  | - 6.2 | - 6.3 |
| Short Circuit Current | ΔI <sub>sc</sub> /ΔT↑ [mA/°C] | 0.32  | 0.33   | 0.31  | 0.39  |
| Voltage at max. Power | ΔV <sub>mp</sub> /ΔT↑ [mV/°C] | - 6.1 | - 6.8  | - 6.3 | - 6.4 |
| Current at max. Power | ΔI <sub>mp</sub> /ΔT↑ [mA/°C] | 0.28  | 0.36   | 0.20  | 0.29  |



### Threshold Values

|              |  |
|--------------|--|
| Absorptivity | ≤ 0.91 (with CMX 100 AR)                             |
| Pull Test    | > 1.6 N at 45° welding test (with 12.5µm Ag stripes) |
| Status       | Qualified  |